Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8027	((high near voltage) near (gate or dielectric or insulat$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 14:33
L2	333	(((high near voltage) near (gate or dielectric or insulat$3))) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 14:40
L3	4025	(implan$3) with (nitrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 14:34
L4	16	(implan$3) with (nitrogen) with (low near3 voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 14:34
L5	18	(implant$3) with (nitrogen) with (low near3 voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 14:41
L6	1	2 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 14:35
L7	4427	(((voltage) near (gate or dielectric or insulat$3))) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:03
L8	5045	(((voltage) near (gate or dielectric or insulat$3 or layer))) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:03
L9	187	(implant$3) with (nitrogen) with (voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:03

L10	8	8 and 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 14:41
L11	17089	(((voltage) near5 (gate or dielectric or insulat$3))) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:03
L12	17346	(((voltage) near3 (gate or dielectric or insulat$3 or layer))) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:03
L13	4628	(implant$3) with (nitrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:04
L14	291	12 and 13 .	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:04
L15	118	14 and (low near3 voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:04
L16	72	15 and (nitrogen) with (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:55
L17	172307	"438"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:05
L18	46	16 and 17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:05
L19	10	16 and (gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 15:57

L20	2	16 and (high near voltage near gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:14
L21	0	(intermediate near core near gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:15
L22	9962	(intermediate near3 core)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:15
L23	3721	(intermediate near core)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:15
L24	0	(intermediate near core near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:17
L25	1	(intermediate near core near3 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:15
L26	0	(intermediate near core) with (gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:16
L27	6	(intermediate near core) with (lv or low near voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:16
L28	0	(low near voltage near core near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:17
L29	198	(low near voltage near core)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:18

L30	16	17 and 29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:18